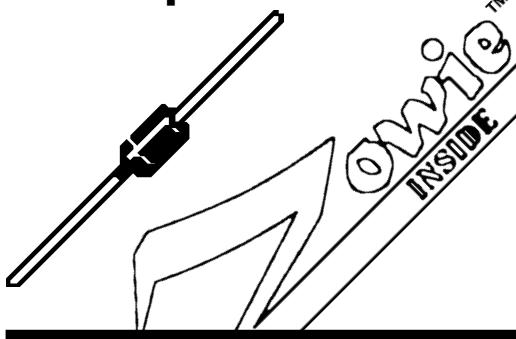


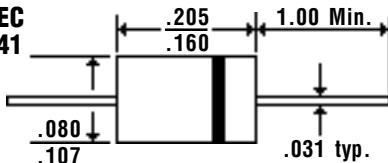


EGPZ10A . . . 10K Series

Description



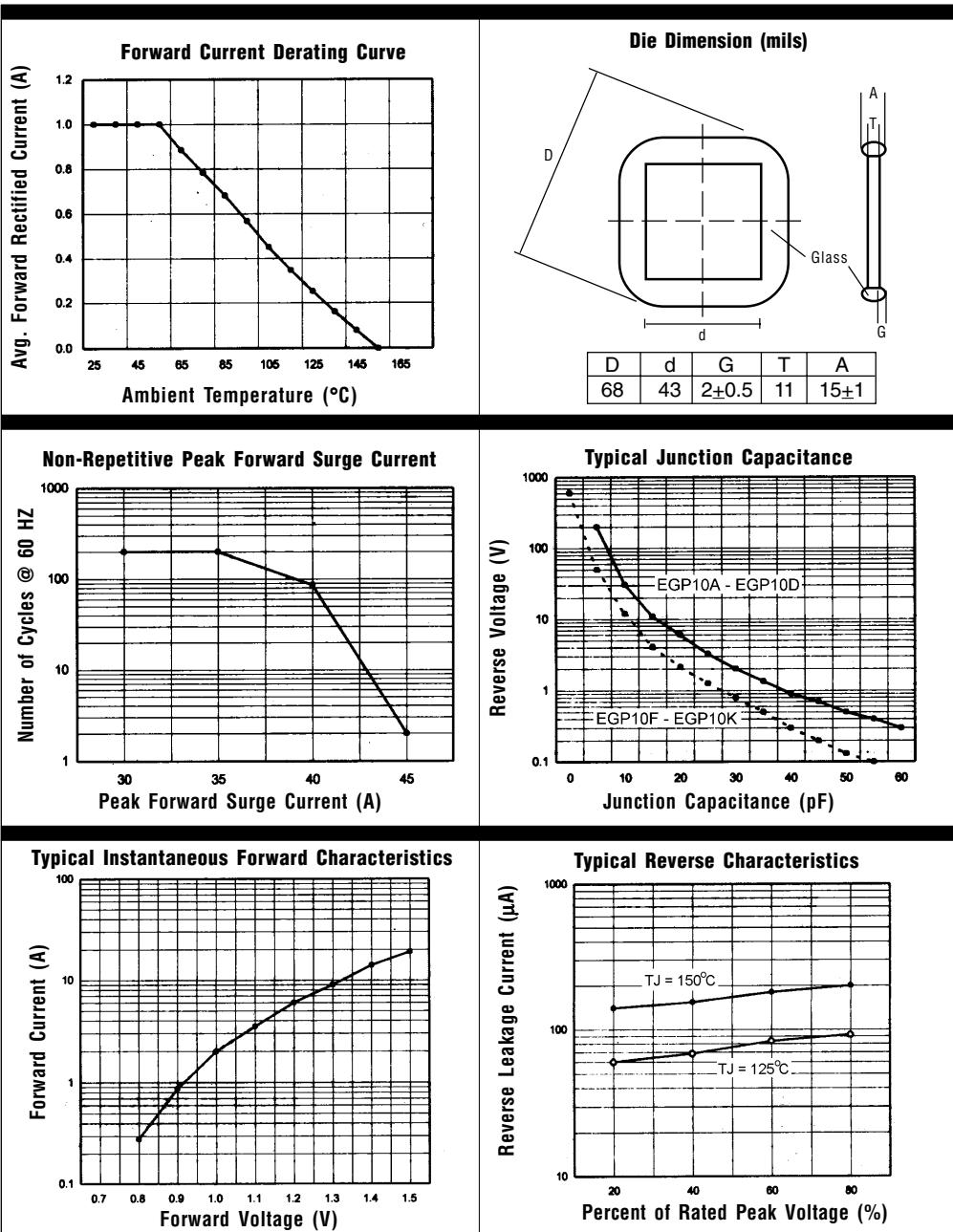
Mechanical Dimensions

JEDEC
DO-41

Features

- LOWEST COST FOR GLASS SINTERED FAST EFFICIENT CONSTRUCTION
- 1.0 AMP OPERATION @ $T_A = 55^\circ\text{C}$, WITH NO THERMAL RUNAWAY
- LOWEST V_F FOR GLASS SINTERED FAST EFFICIENT CONSTRUCTION
- SINTERED GLASS CAVITY-FREE JUNCTION
- TYPICAL I_R < 100 nAmps

Electrical Characteristics @ 25°C.						EGPZ10A . . . 10K Series	Units
Maximum Ratings	10A	10B	10D	10G	10J	10K	
Peak Repetitive Reverse Voltage...V _{RRM}	50	100	200	400	600	800	Volts
RMS Reverse Voltage...V _{R(rms)}	35	70	140	280	420	560	Volts
DC Blocking Voltage...V _{DC}	50	100	200	400	600	800	Volts
Average Forward Rectified Current...I _{F(av)} Current 3/8" Lead Length @ $T_A = 55^\circ\text{C}$	1.0	Amps
Non-Repetitive Peak Forward Surge Current...I _{FSM} 8.3mS, ½ Sine Wave Superimposed on Rated Load	30	Amps
Forward Voltage @ 1.0A...V _F	< 1.0	> 1.3	< 1.7	>			Volts
DC Reverse Current...I _{R(max)} @ Rated DC Blocking Voltage	$T_A = 25^\circ\text{C}$	5.0			μAmps
	$T_A = 125^\circ\text{C}$	100			μAmps
Typical Junction Capacitance...C _J (Note 1)	15	pF
Maximum Thermal Resistance...R _{θJA} (Note 2)	55	°C/W
Maximum Reverse Recovery Time...t _{RR} (Note 3)	< 50	> < 75	>				nS
Operating & Storage Temperature Range...T _j , T _{STRG}	-65 to 150	°C



- NOTES:**
1. Measured @ 1 MHZ and applied reverse voltage of 4.0V.
 2. Thermal Resistance from Junction to Ambient at 3/8" Lead Length, P.C. Board Mounted.
 3. Reverse Recovery Condition $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$.